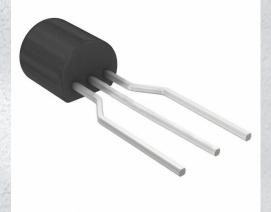


# PN4249\_D75Z Datasheet

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ii Electronics Part Number	PN4249_D75Z-DG
Manufacturer	onsemi
ufacturer Product Number	PN4249_D75Z
Description	TRANS PNP 60V 0.5A TO92-3
Detailed Description	Bipolar (BJT) Transistor PNP 60 V 500 mA 625 mW T hrough Hole TO-92-3

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# Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PN4249_D75Z	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
PNP	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
60 V	250mV @ 500μA, 10mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
10nA (ICBO)	100 @ 100μA, 5V
Power - Max:	Frequency - Transition:
625 mW	
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 (TO-226AA) Formed Leads	TO-92-3
Base Product Number:	
PN424	

# **Environmental & Export classification**

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.21.0095



from Process 68. See PN200 for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V
Vcbo	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
lc	Collector Current - Continuous	500	mA
TJ, Tstg	Operating and Storage Junction Temperature Range	-55 to +150	٥°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

## NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics

Symbol	Characteristic	Мах	Units
		PN4249	
P <sub>D</sub>	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
R <sub>0JC</sub>	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

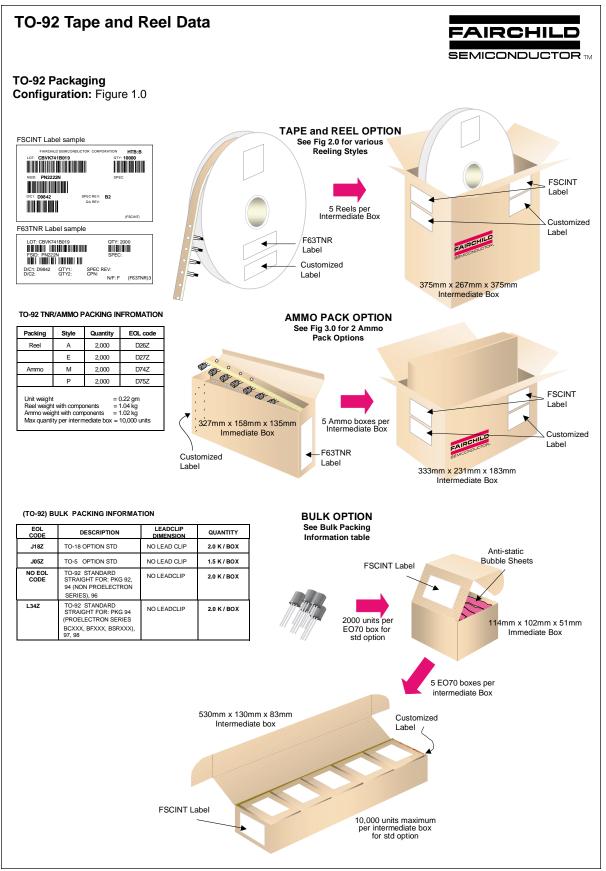
TA = 25°C unless otherwise noted

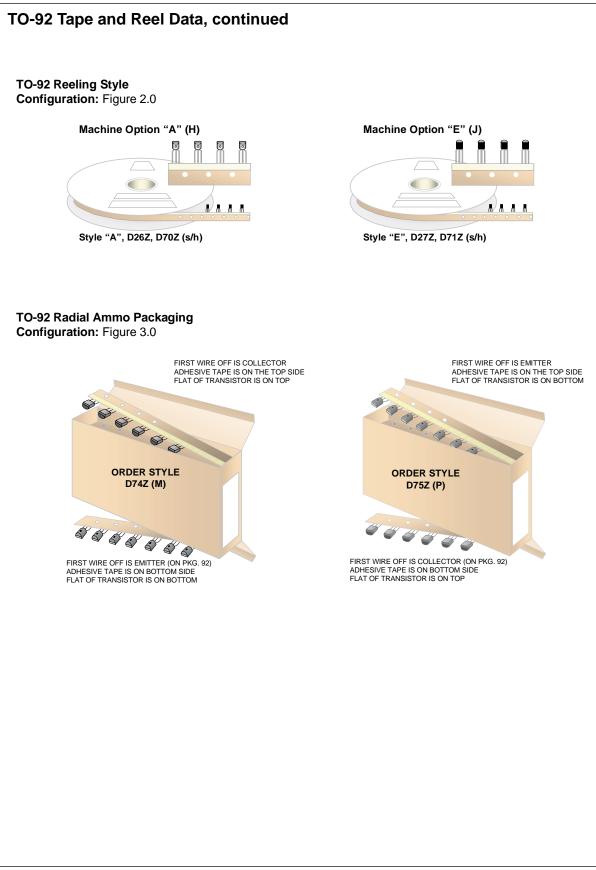
**PN4249** 

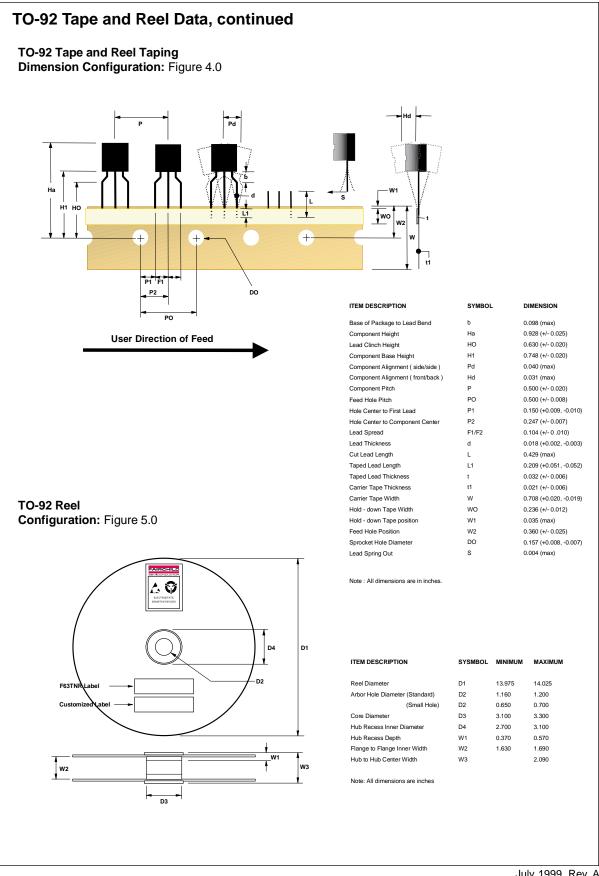
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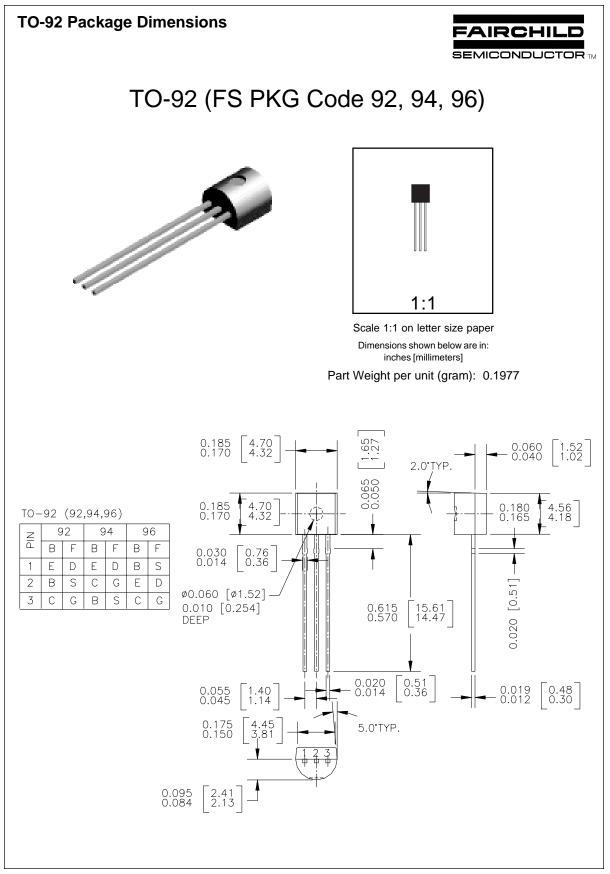
					(continue
Electrical Characteristics   TA = 25°C unless otherwise noted     Symbol   Parameter   Test Conditions   Min   Max   Units					
OFF CHA	RACTERISTICS		1		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 5.0 \text{ mA}, I_{\rm B} = 0$	60		V
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage*	$I_{C} = 10 \ \mu A, \ I_{B} = 0$	60		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 10 \ \mu A, I_{E} = 0$	60		V
/ <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \ \mu A, \ I_C = 0$	5.0		V
СВО	Collector-Cutoff Current	$V_{CB} = 40 \text{ V}, I_E = 0$		10	nA
EBO	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		20	nA
ON CHAR	ACTERISTICS*				
ON CHAR h <sub>FE</sub> V <sub>CE(sat)</sub>	ACTERISTICS* DC Current Gain Collector-Emitter Saturation Voltage	$V_{CE} = 5.0 \text{ V}, \text{ Ic} = 100 \ \mu\text{A}$ Ic = 10 mA, I <sub>B</sub> = 0.5 mA	100	300 0.25	V
n <sub>FE</sub> V <sub>CE(sat)</sub> SMALL S	DC Current Gain Collector-Emitter Saturation Voltage	Ic = 10 mA, I <sub>B</sub> = 0.5 mA	100		
DFE /CE(sat) SMALL S Cob	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	2.5	0.25	pF
DFE /CE(sat) SMALL S Cob	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance Input Impedance	Ic = 10 mA, I <sub>B</sub> = 0.5 mA		0.25 6.0	
∩ <sub>FE</sub> V <sub>CE(sat)</sub>	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA},$	2.5	0.25 6.0 17	pF kΩ

PN4249









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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.
	•	Rev. G



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